

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

LISTING OF CLAIMS:

Claims 1 and 2. (Cancelled)

3. (previously presented): A semiconductor device comprising:

a first semiconductor chip which has a first surface;

an external connecting terminal which is formed on said first surface, said external connecting terminal having a primary height with respect to said first surface;

a second semiconductor chip which is mounted on said first surface through a bump, said second semiconductor chip having a secondary height with respect to said first surface;

a rewiring which electrically connects said first semiconductor chip, said second semiconductor chip, and said external connecting terminal with each other and which is located on said first surface;

an insulating layer which is overlaid on said rewiring and which has predetermined opening portions in a first region for forming said external connecting terminal and in a second region for mounting said second semiconductor chip, respectively; and

bedding electrodes which are formed in said predetermined opening portions respectively, said external connecting terminal comprising BGA and being positioned on said bedding electrode in said first region, said second semiconductor chip being flip chip bonded to said bedding electrode in said second region through said bump,

wherein said second semiconductor chip is thin whereby said secondary height is smaller than said primary height.

4. (Original) A semiconductor device as claimed in claim 3, wherein said insulating layer is made of at least two resins of which elastic characteristics are different from each other, one resin being in said first region while another resin being in said second region.

5. (Original) A semiconductor device as claimed in claim 3, wherein both said bedding electrode in said first region and said bedding electrode in said second region are made of the same material provided in the same process.

6. (Original) A semiconductor device as claimed in claim 4, wherein both said bedding electrode in said first region and said bedding electrode in said second region are made of the same material provided in the same process.

7. (Original) A semiconductor device as claimed in claim 3, wherein said bedding electrode in said first region and said bedding electrode in said second region are made of different materials from each other.

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8. (Original) A semiconductor device as claimed in claim 4, wherein said bedding electrode in said first region and said bedding electrode in said second region are made of different materials from each other.

9. (Original) A semiconductor device as claimed in claim 6, wherein a film including a material different from that of said bedding electrode is stacked on said bedding electrode.

10. (Original) A semiconductor device as claimed in claim 8, wherein a film including a material different from that of said bedding electrode is stacked on said bedding electrode.

11. (Currently Amended) A semiconductor device ~~as claimed in claim 1~~ comprising:
a first semiconductor chip which has a first surface;
an external connecting terminal which is formed on said first surface, said external
connecting terminal having a primary height with respect to said first surface;
a second semiconductor chip which is mounted on said first surface,
wherein said second semiconductor chip has a secondary height with respect to said first
surface; and
said secondary height is smaller than said primary height,
wherein said second semiconductor chip further comprises a projection on another surface thereof opposite to a junction surface mounted to said first semiconductor chip, said

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projection having a ternary height with respect to said another surface of said second semiconductor chip; and said ternary height being determined so that said primary height being substantially equal to the sum of said secondary height and said ternary height.

12. (Original) A semiconductor device as claimed in claim 11, wherein said projection is made of a material selected from the group consisting of metal, conductive resin, and insulating resin.

13. (Original) A semiconductor device as claimed in claim 11, wherein said junction surface of said second semiconductor chip mounted to said first semiconductor chip through said bump is sealed by resin.

14. (Original) A semiconductor device as claimed in claim 3, further comprising a resin layer which is provided on said bedding electrode in said first region and which includes via hole penetrating to the bedding electrode in said first region, and a conductor which is buried into said via hole and which electrically connects said external connecting terminal with the bedding electrode in said first region.

Claims 15-29 (Cancelled)